

Author details

[Back to results](#) | 1 of 2 [Next >](#)
[Print](#) | [E-mail](#)

Taur, Yuan

University of California, San Diego, Department of
Electrical & Computer Engineering, San Diego,
United States

Author ID: 7005521684

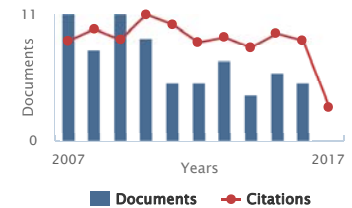
[About Scopus Author Identifier](#) | [View potential author matches](#)

Other name formats: Taur, Y.

Documents: 195
Citations: 7383 total citations by 5571 documents
h-index: 41
Co-authors: 150 (maximum 150 co-authors can be displayed)
Subject area: Engineering , Materials Science [View More](#)

[Analyze author output](#)
[View citation overview](#)
[View h-graph](#)
[Follow this Author](#)

Receive emails when this author publishes new articles

[Get citation alerts](#)
[Add to ORCID](#)
[Request author detail corrections](#)
[Export profile to SciVal](#)


195 Documents | Cited by 5571 documents | 150 co-authors

195 documents [View all in search results format](#)

Sort on: [Date](#) [Cited by](#) [...](#)

[Export all](#) | [Add all to list](#) | [Set document alert](#) | [Set document feed](#)

A short-channel 1-V model for 2-D MOSFETs	Taur, Y., Wu, J., Min, J.	2016	IEEE Transactions on Electron Devices	3
View at Publisher Find it NTU				
Characterization of interface defects in ALD Al ₂ O ₃ /p-GaSb MOS capacitors using admittance measurements in range from kHz to GHz	Gu, S., Min, J., Taur, Y., Asbeck, P.M.	2016	Solid-State Electronics	1
View at Publisher Find it NTU				
A continuous semianalytic current model for DG and NW TFETs	Wu, J., Taur, Y.	2016	IEEE Transactions on Electron Devices	3
View at Publisher Find it NTU				
Dimensionality dependence of TFET performance down to 0.1 V supply voltage	Taur, Y., Wu, J., Min, J.	2016	IEEE Transactions on Electron Devices	4
View at Publisher Find it NTU				
Reduction of TFET OFF-Current and Subthreshold Swing by Lightly Doped Drain	Wu, J., Taur, Y.	2016	IEEE Transactions on Electron Devices	0
View at Publisher Find it NTU				
Analysis of Source Doping Effect in Tunnel FETs with Staggered Bandgap	Min, J., Wu, J., Taur, Y.	2015	IEEE Electron Device Letters	9
View at Publisher Find it NTU				
Short-Channel Effects in Tunnel FETs	Wu, J., Min, J., Taur, Y.	2015	IEEE Transactions on Electron Devices	9
View at Publisher Find it NTU				
An analytic model for heterojunction and homojunction tunnel FETs with 3D density of states	Wu, J., Min, J., Ji, J., Taur, Y.	2015	Device Research Conference - Conference Digest, DRC	4
View at Publisher Find it NTU				
An analytic model for heterojunction tunnel FETs with exponential barrier	Taur, Y., Wu, J., Min, J.	2015	IEEE Transactions on Electron Devices	10
View at Publisher Find it NTU				
A Unified Two-Band Model for Oxide Traps and Interface States in MOS Capacitors	Taur, Y., Chen, H., Xie, Q., (...), Vais, A., Veksler, D.	2015	IEEE Transactions on Electron Devices	0
Article in Press				
View at Publisher Find it NTU				

Author History

Publication range: 1974 - 2016

References: [1342](#)

Source history:

International Conference on Solid-State and Integrated C Technology Proceedings [View docu](#)

IEEE Journal of Solid-State Circuits [View docu](#)

Journal of Computational Electronics [View docu](#)

[View More](#)

[Show Related Affiliations](#)

A unified two-band model for oxide traps and interface states in MOS capacitors	Taur, Y., Chen, H.-P., Xie, Q., (...), Vais, A., Veksler, D.	2015	IEEE Transactions on Electron Devices	3
View at Publisher Find it NTU				
Diameter-independent hole mobility in Ge/Si Core/shell nanowire field effect transistors	Nguyen, B.-M., Taur, Y., Picraux, S.T., Dayeh, S.A.	2014	Nano Letters	14
View at Publisher Find it NTU				
Effects of oxide thickness and temperature on dispersions in InGaAs MOS C-V characteristics	Chen, H.-P., Ahn, J., McIntyre, P.C., Taur, Y.	2014	Journal of Vacuum Science and Technology B: Microelectronics and Nanometer Structures	7
View at Publisher Find it NTU				
Modeling illumination effects on n- and p-Type InGaAs MOS at room and low temperatures	Chen, H.-P., Veksler, D., Bersuker, G., Taur, Y.	2014	IEEE Transactions on Electron Devices	3
View at Publisher Find it NTU				
Determination of energy and spatial distribution of oxide border traps in In _{0.53} Ga _{0.47} As MOS capacitors from capacitance-voltage characteristics measured at various temperatures	Dou, C., Lin, D., Vais, A., (...), Thean, A., Groeseneken, G.	2014	Microelectronics Reliability	9
View at Publisher Find it NTU				
Comparison of bulk-oxide trap models: Lumped versus distributed circuit	Chen, H.-P., Ahn, J., McIntyre, P.C., Taur, Y.	2013	IEEE Transactions on Electron Devices	10
View at Publisher Find it NTU				
Comments to 'A distributive-transconductance model for border traps in III-V/High-k MOS capacitors'	Taur, Y., Chen, H.-P., Yuan, Y., Yu, B.	2013	IEEE Electron Device Letters	1
View at Publisher Find it NTU				
Comments to 'A distributive-transconductance model for border traps in III-V/High-k MOS capacitors'	Taur, Y., Chen, H.-P., Yuan, Y., Yu, B.	2013	IEEE Electron Device Letters	1
View at Publisher Find it NTU				
Re-examination of the extraction of MOS interface-state density by C-V stretchout and conductance methods	Chen, H.-P., Yuan, Y., Yu, B., (...), Wann, C., Taur, Y.	2013	Semiconductor Science and Technology	7
View at Publisher Find it NTU				
Comprehensive analysis of short-channel effects in ultrathin SOI MOSFETs	Xie, Q., Lee, C.-J., Xu, J., (...), Sun, J.Y.-C., Taur, Y.	2013	IEEE Transactions on Electron Devices	22
View at Publisher Find it NTU				

Display: results per page

Page 1

[Back to results](#) | 1 of 2 [Next >](#)[Top of page](#)

The data displayed above is compiled exclusively from articles published in the Scopus database. To request corrections to any inaccuracies or provide any further feedback, please [contact us](#) (registration required).
The data displayed above is subject to the privacy conditions contained in the [privacy policy](#).

About Scopus

[What is Scopus](#)
[Content coverage](#)
[Scopus blog](#)
[Scopus API](#)
[Privacy matters](#)

Language

[日本語に切り替える](#)
[切换到简体中文](#)
[切换到繁體中文](#)

Customer Service

[Help](#)
[Contact us](#)

ELSEVIER[Terms and conditions](#) [Privacy policy](#)Copyright © 2017 [Elsevier B.V.](#) All rights reserved. Scopus® is a registered trademark of Elsevier B.V.Cookies are set by this site. To decline them or learn more, visit our [Cookies page](#). RELX Group

